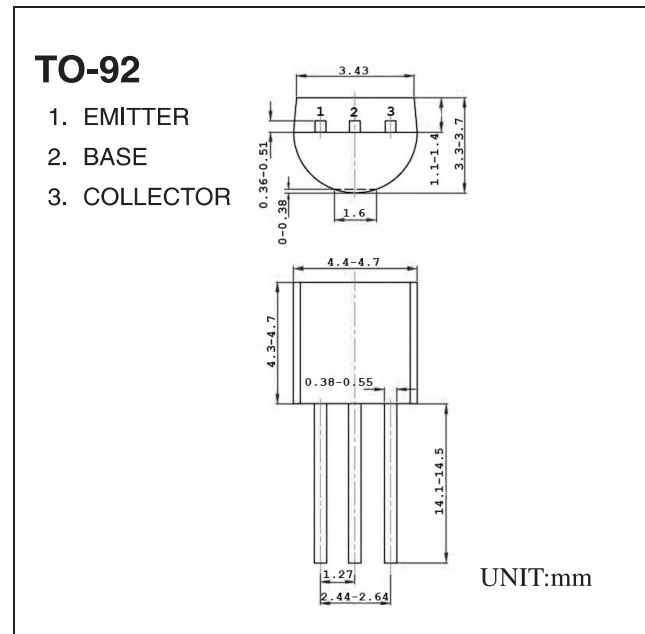


TRANSISTOR (PNP)
Plastic-Encapsulate Transistor

FEATURES	
Power dissipation	P_{CM} : 0.625W ($T_{amb}=25^{\circ}C$)
Collector current	I_{CM} : -0.6A
Collector-base voltage	$V_{(BR)CBO}$: -60V
Operating and storage junction temperature range	T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS
 Ratings at $25^{\circ}C$ ambient temperature unless otherwise specified.

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10 \mu A, I_E=0$	-60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-60		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10 \mu A, I_C=0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB}=-50V, I_E=0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-50V, I_B=0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-3V, I_C=0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-10V, I_C=-150mA$	100	300	
	$h_{FE(2)}$	$V_{CE}=-10V, I_C=-1mA$	60		
Collector-emitter saturation voltage	V_{CEsat}	$I_C=-500mA, I_B=-50mA$		-1	V
Base-emitter saturation voltage	V_{BEsat}	$I_C=-500mA, I_B=-50mA$		-2	V
Transition frequency	f_r	$V_{CE}=-20V, I_C=-50mA$ $f=100MHz$	200		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	L	H
Range	100-200	200-300